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Sheet 1 of 1

Complete if Known	
Application Number	TBD
Filing Date	Herewith
First Named Inventor	Yeo, *et al.*
Art Unit	TBD
Examiner Name	TBD
Attorney Docket Number	TSM03-0511

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number - Kind Code[2] (*if known*)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A	US-6,252,284 B1	06-26-2001	Muller, *et al.*	
	B	US-6,391,695 B1	05-21-2002	Yu	
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Examiner Initials*	Cite No.[1]	Foreign Patent Document Country Code[3] - Number[4] - Kind Code[5] (*if known*)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
	H	HUANG, X., et al. "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5 (May 2001) pp. 880-886.	
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	N	LEOBANDUNG, E. "Wire-Channel and wrap-around-gate metal-oxide-semiconductor field-effect transistors with a significant reduction of short channel effects," Journal of Vacuum Science and Technology, Vol. B15, No. 6, (November/December 1997) pp. 2791-2794.	

Examiner Signature		Date Considered	8/31/04

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